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				Art Unit	2811
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Sheet	1	of	7	Attorney Docket Number .	740756-2646

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		JP 62-244165	10/24/1987			Abstract
		JP 01-187873	07/27/1989		<del></del> ,	Abstract
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include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the nitials No. item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
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<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not I conformance and not considered. Include copy of this form with next communication to applicant.

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			U.S. PATENT DOC	UMENTS	<u> </u>	.p. 261	<u> </u>
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	4,377,421	03/22/83	Wada et al	<del></del>			appropriate)
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